

XP162A12A6PR-G

ETR11026-004

Power MOSFET

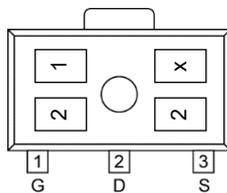
■ GENERAL DESCRIPTION

The XP162A12A6PR is a P-channel Power MOSFET with low on-state resistance and ultra high-speed switching characteristics. Because high-speed switching is possible, the IC can be efficiently set thereby saving energy. A gate protect diode is built-in to prevent static damage. The small SOT-89 package makes high density mounting possible.

■ APPLICATIONS

- Notebook PCs
- Cellular and portable phones
- On-board power supplies
- Li-ion battery systems

■ PIN CONFIGURATION/ MARKING

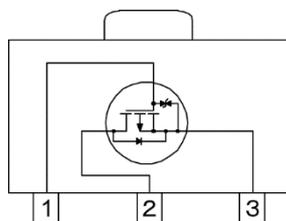


SOT-89
(TOP VIEW)

G : Gate
S : Source
D : Drain

* x represents production lot number.

■ EQUIVALENT CIRCUIT



P-channel MOSFET
(1 device built-in)

■ FEATURES

Low On-State Resistance : $R_{ds(on)}=0.17\Omega @V_{gs}=-4.5V$
: $R_{ds(on)}=0.3\Omega @V_{gs}=-2.5V$

Ultra High-Speed Switching

Driving Voltage : -2.5V

Gate Protect Diode Built-in

P-Channel Power MOSFET

DMOS Structure

Package : SOT-89

■ PRODUCT NAME

PRODUCT	PACKAGE	ORDER UNIT
XP162A12A6PR-G*	SOT-89	1,000pcs/Reel

(*) The "-G" suffix denotes Halogen and Antimony free as well as being fully RoHS compliant

■ ABSOLUTE MAXIMUM RATINGS

$T_a = 25^\circ\text{C}$

PARAMETER	SYMBOL	RATINGS	UNITS
Drain-Source Voltage	V_{dss}	-20	V
Gate-Source Voltage	V_{gss}	± 12	V
Drain Current (DC)	I_d	-2.5	A
Drain Current (Pulse)	I_{dp}	-10	A
Reverse Drain Current	I_{dr}	-2.5	A
Channel Power Dissipation *	P_d	2	W
Channel Temperature	T_{ch}	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55~150	$^\circ\text{C}$

* When implemented on a ceramic PCB (900mm² x 0.8mm)

ELECTRICAL CHARACTERISTICS

DC Characteristics

Ta = 25°C

PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Drain Cut-Off Current	Idss	Vds= -20V, Vgs= 0V	-	-	-10	μA
Gate-Source Leak Current	Igss	Vgs= ±12V, Vds= 0V	-	-	±10	μA
Gate-Source Cut-Off Voltage	Vgs(off)	Id=-1mA, Vds= -10V	-0.5	-	-1.2	V
Drain-Source On-State Resistance*1	Rds(on)	Id=-1.5A, Vgs= -4.5V	-	0.13	0.17	Ω
		Id=-1.5A, Vgs= -2.5V	-	0.22	0.30	Ω
Forward Transfer Admittance*1	Yfs	Id=-1.5A, Vds= -10V	-	4	-	S
Body Drain Diode Forward Voltage	Vf	If= -2.5A, Vgs= 0V	-	-0.85	-1.1	V

*1 Effective during pulse test.

Dynamic Characteristics

Ta = 25°C

PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Input Capacitance	Ciss	Vds=-10V, Vgs=0V f= 1MHz	-	310	-	pF
Output Capacitance	Coss		-	200	-	pF
Feedback Capacitance	Crss		-	90	-	pF

Switching Characteristics

Ta = 25°C

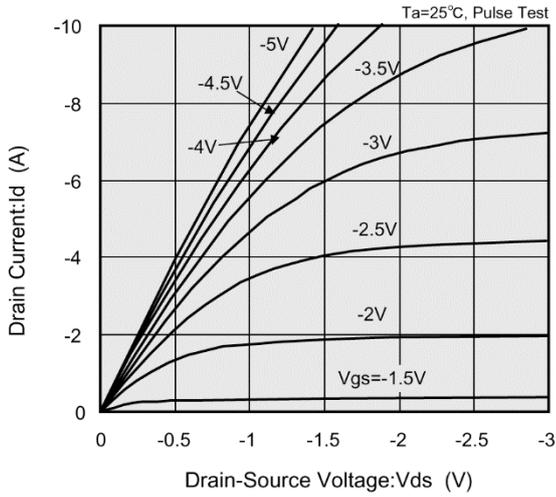
PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Turn-On Delay Time	td (on)	Vgs= -5V, Id= -1.5A Vdd= -10V	-	5	-	ns
Rise Time	tr		-	15	-	ns
Turn-Off Delay Time	td (off)		-	55	-	ns
Fall Time	tf		-	55	-	ns

Thermal Characteristics

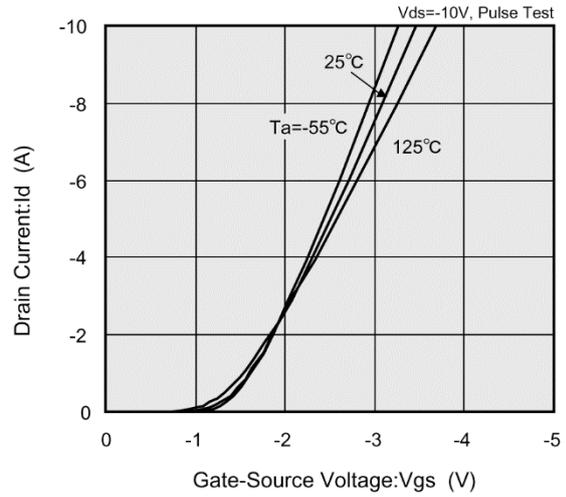
PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Thermal Resistance (Channel-Ambience)	Rth (ch-a)	Implement on a ceramic PCB	-	62.5	-	°C/W

TYPICAL PERFORMANCE CHARACTERISTICS

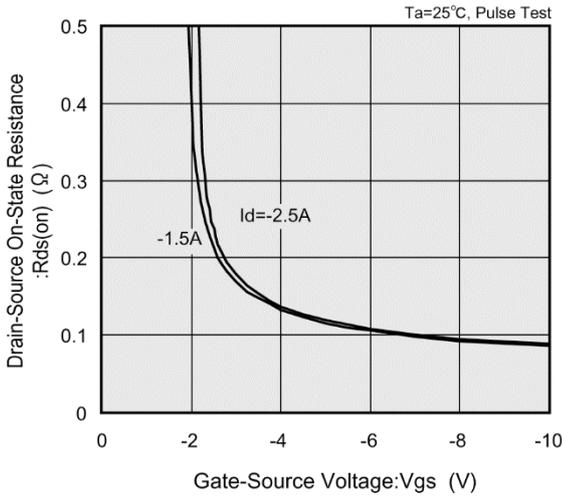
(1) Drain Current vs. Drain-Source Voltage



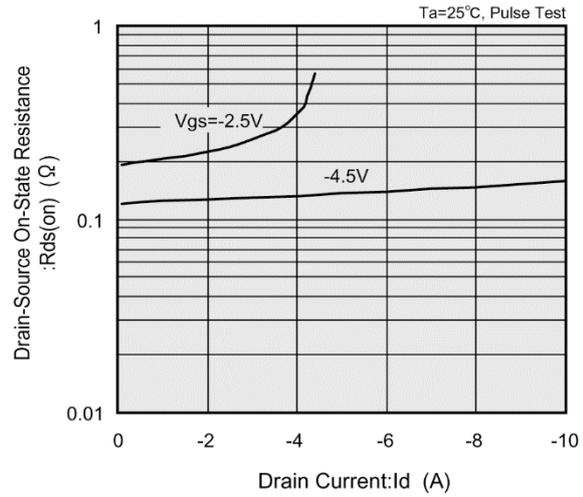
(2) Drain Current vs. Gate-Source Voltage



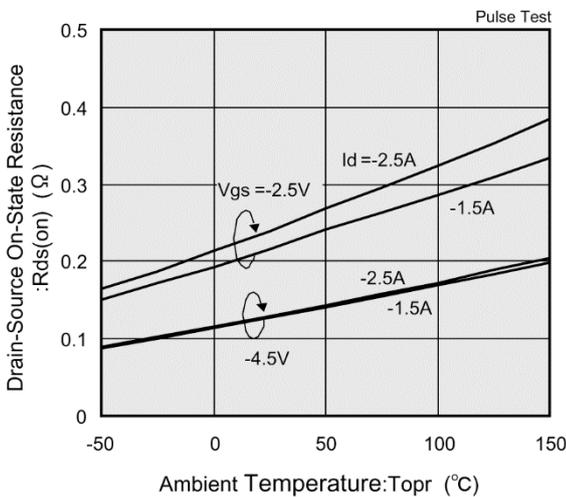
(3) Drain-Source On-State Resistance vs. Gate-Source Voltage



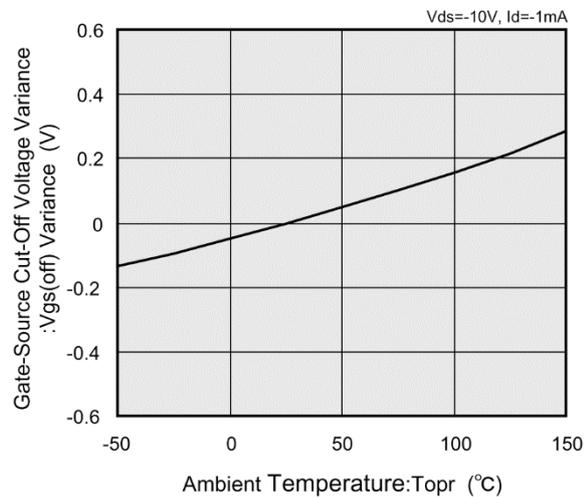
(4) Drain-Source On-State Resistance vs. Drain Current



(5) Drain-Source On-State Resistance vs. Ambient Temperature

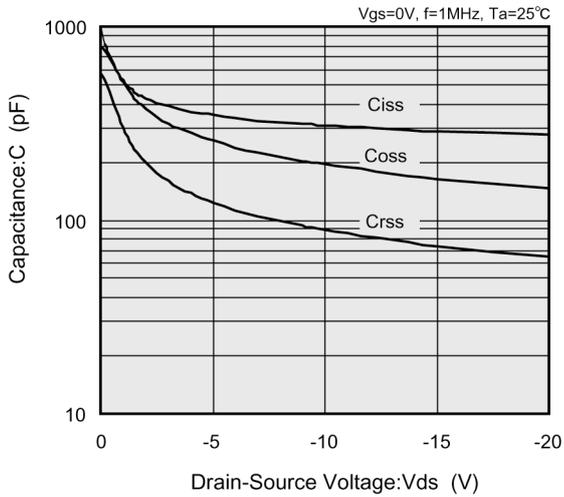


(6) Gate-Source Cut-Off Voltage Variance vs. Ambient Temperature

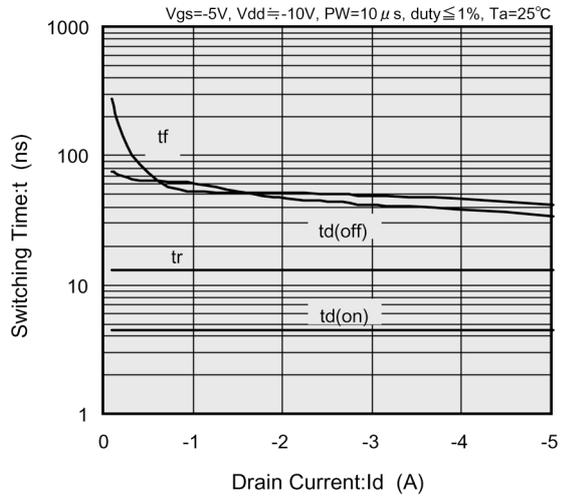


TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

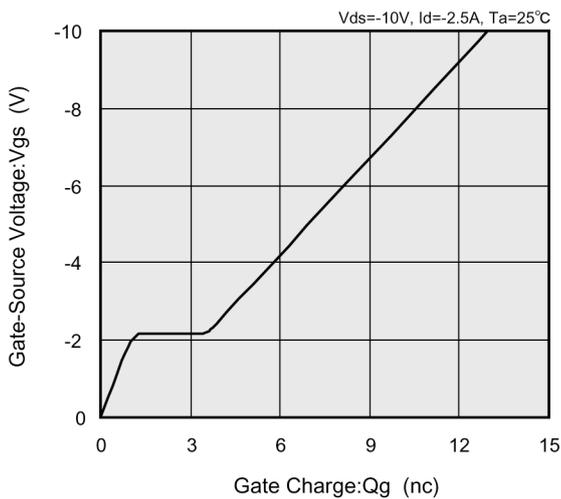
(7) Capacitance vs. Drain-Source Voltage



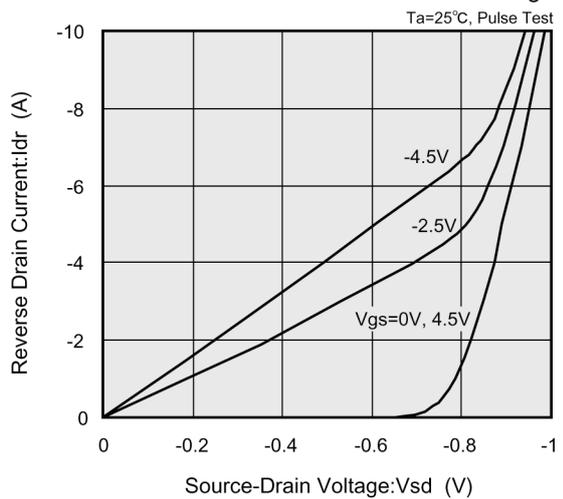
(8) Switching Time vs. Drain Current



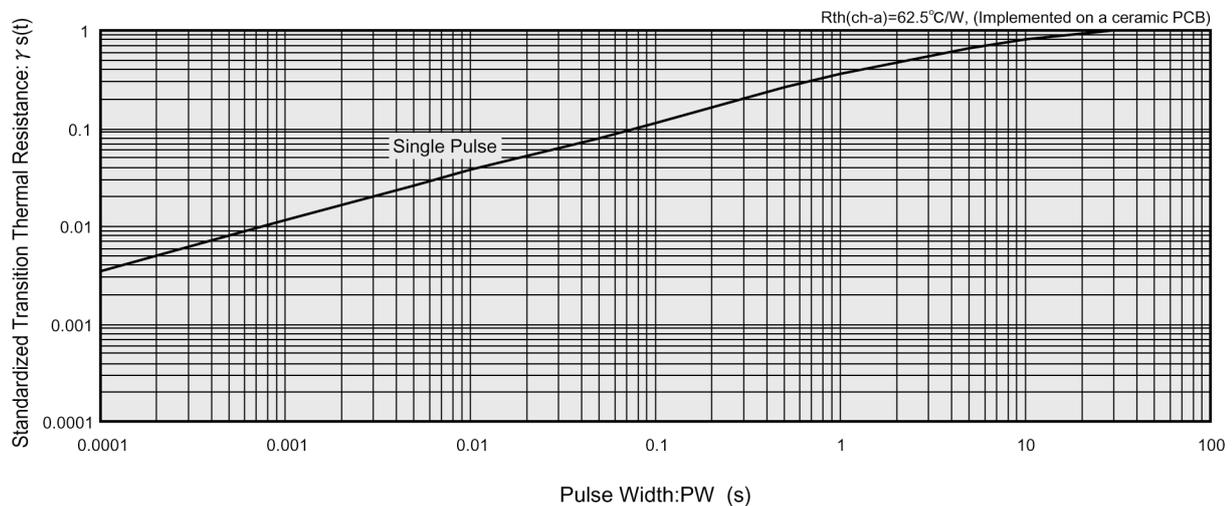
(9) Gate-Source Voltage vs. Gate Charge



(10) Reverse Drain Current vs. Source-Drain Voltage



(11) Standardized transition Thermal Resistance vs. Pulse Width



■ PACKAGING INFORMATION

For the latest package information go to, www.torexsemi.com/technical-support/packages

PACKAGE	OUTLINE / LAND PATTERN	THERMAL CHARACTERISTICS
SOT-89	SOT-89 PKG	SOT-89 Power Dissipation

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